

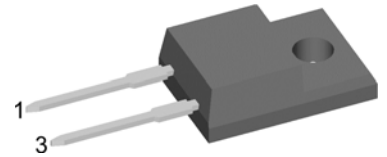
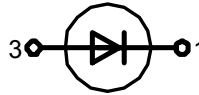
# Sonic-FRD

High Performance Fast Recovery Diode  
 Low Loss and Soft Recovery  
 Single Diode

$V_{RRM} = 1200\text{ V}$   
 $I_{FAV} = 10\text{ A}$   
 $t_{rr} = 75\text{ ns}$

Part number

**DHG 10 I 1200PM**



Backside: isolated

**Features / Advantages:**

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low  $I_{rm}$ -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{rm}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

**Applications:**

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

**Package:**

- TO-220FPAC
- Industry standard outline
  - Plastic overmolded tab for electrical isolation
  - Epoxy meets UL 94V-0
  - RoHS compliant

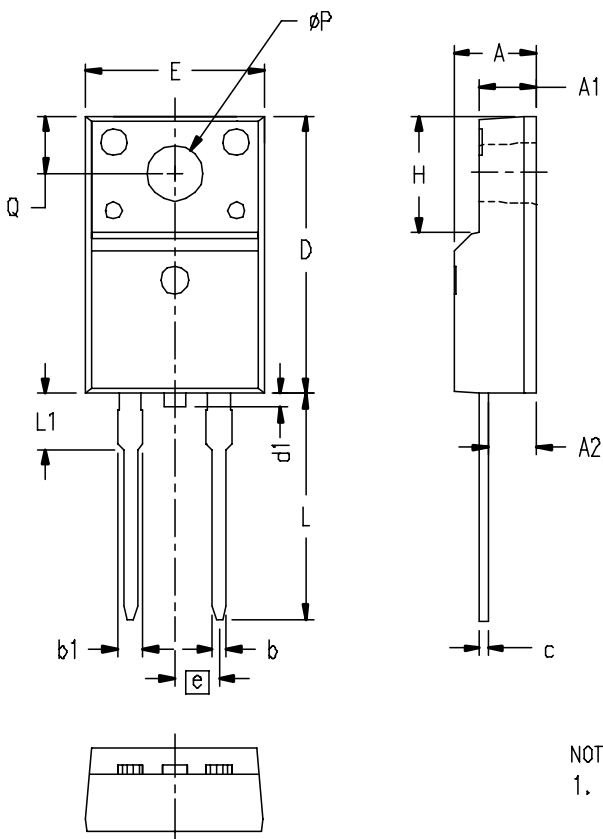
**Ratings**

Symbol	Definition	Conditions	Ratings			Unit	
			min.	typ.	max.		
$V_{RRM}$	max. repetitive reverse voltage	$T_{VJ} = 25\text{ °C}$			1200	V	
$I_R$	reverse current	$V_R = 1200\text{ V}$			15	$\mu\text{A}$	
		$V_R = 1200\text{ V}$			1.5	mA	
$V_F$	forward voltage	$I_F = 10\text{ A}$			2.69	V	
		$I_F = 20\text{ A}$			3.56	V	
		$I_F = 10\text{ A}$	$T_{VJ} = 125\text{ °C}$			2.38	V
		$I_F = 20\text{ A}$	$T_{VJ} = 125\text{ °C}$			3.33	V
$I_{FAV}$	average forward current	rectangular, $d = 0.5$			10	A	
$V_{F0}$	threshold voltage	} for power loss calculation only			1.60	V	
$r_F$	slope resistance				73.6	$\text{m}\Omega$	
$R_{thJC}$	thermal resistance junction to case				4.00	K/W	
$T_{VJ}$	virtual junction temperature		-55		150	$^{\circ}\text{C}$	
$P_{tot}$	total power dissipation				31	W	
$I_{FSM}$	max. forward surge current	$t_p = 10\text{ ms (50 Hz), sine}$			70	A	
$I_{RM}$	max. reverse recovery current	$I_F = 10\text{ A};$		8.5		A	
		$-di_F/dt = 350\text{ A}/\mu\text{s}$				A	
$t_{rr}$	reverse recovery time	$V_R = 800\text{ V}$		75		ns	
						ns	
$C_J$	junction capacitance	$V_R = 600\text{ V}; f = 1\text{ MHz}$		tbd		pF	
$E_{AS}$	non-repetitive avalanche energy	$I_{AS} = \text{tbd A}; L = 100\text{ }\mu\text{H}$			tbd	mJ	
$I_{AR}$	repetitive avalanche current	$V_A = 1.5 \cdot V_R \text{ typ.}; f = 10\text{ kHz}$			tbd	A	

Symbol	Definition	Conditions	Ratings			Unit
			min.	typ.	max.	
$I_{RMS}$	RMS current	per pin*			35	A
$R_{thCH}$	thermal resistance case to heatsink			0.50		K/W
$M_D$	mounting torque		0.4		0.6	Nm
$F_c$	mounting force with clip		20		60	N
$T_{sta}$	storage temperature		-55		150	°C
<b>Weight</b>				2		g

\* Irms is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip.

In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.

**Outlines TO-220FPAC**


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
d1	0	.043	0	1.10
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
$\varnothing P$	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40

**NOTE:**

1. All metal surface are matte pure tin plated except trimmed area.